

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-5 (Cancelled).

Claim 6 (Currently amended): An ultrasonic sensor comprising:

a γ -Al₂O₃ single crystal film epitaxially grown on a semiconductor single crystal substrate;

an epitaxial single crystal Pt ~~electrically conductive~~ thin film disposed on the γ -Al₂O₃ single crystal film;

a highly oriented ferroelectric thin film disposed on the epitaxial single crystal ~~electrically conductive~~ Pt thin film; and

an upper electrode disposed on the ferroelectric thin film; wherein the semiconductor single crystal substrate is subjected to a treatment for adjusting a resonant frequency and an ultrasonic wave is to be detected.

Claim 7 (Previously presented): The ultrasonic sensor according to Claim 6, wherein the semiconductor single crystal substrate has an SOI structure.

Claims 8-11 (Cancelled).

Claim 12 (Previously presented): The ultrasonic sensor according to Claim 6, wherein the semiconductor single crystal substrate is a Si single crystal.

Claim 13 (Previously presented): The ultrasonic sensor according to Claim 12, wherein the γ -Al₂O₃ single crystal film epitaxially grown on a semiconductor single crystal substrate is grown on a (100) face of the Si single crystal.

Claim 14 (Currently amended): The ultrasonic sensor according to Claim 6 wherein the highly oriented ferroelectric thin film disposed on the epitaxial single crystal Pt ~~electrically conductive~~ thin film comprises one selected from the group consisting of BaMgF₄, Bi₄Ti₃O₁₂, (Bi,La)₄Ti₃O₁₂, BaTiO₃, Ba_xSr_{1-x}TiO₃, SrBi₂Ta₂O₉, PbTiO₃, Pb_yLa_{1-y}Zr_xTi_{1-x}O₃, and ZnO.

Claim 15 (Previously presented): The ultrasonic sensor according to Claim 6 wherein the upper electrode disposed on the ferroelectric thin film comprises gold black.